Silicon PNP Power Transistors 2SB1657

DESCRIPTION

·With TO-126 package
·Low collector saturation voltage
·High DC current gain

APPLICATIONS

·For audio frequency amplifier
and switching applications

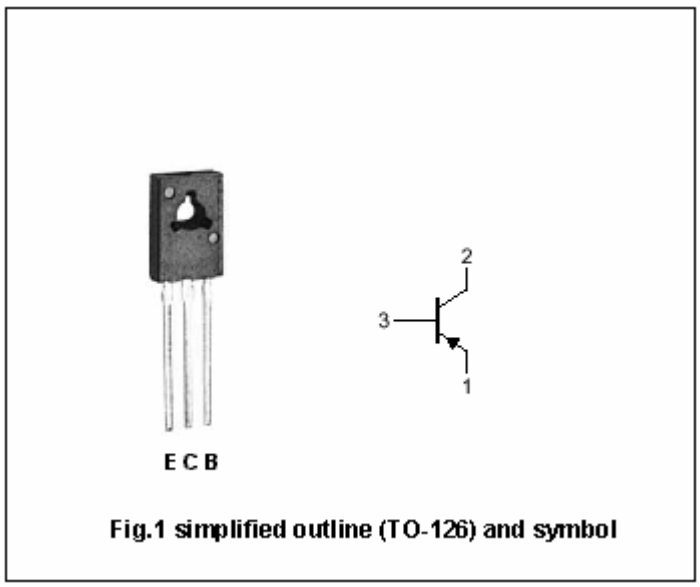

Fig.1 simplified outline (TO-126) and symbol

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-30	V
V_{CEO}	Collector-emitter voltage	Open base	-30	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current (DC)		-5	A
I_{CM}	Collector current-Peak		-8	A
I_B	Base current (DC)		-1	A
P_T	Total power dissipation	T_a=25□	0.1	W
		T_C=25□	10	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA ;I_B=0	-30			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	I_C=-0.5A; I_B=-25mA			-0.15	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	I_C=-1A; I_B=-50mA			-0.25	V
$V_{CEsat-3}$	Collector-emitter saturation voltage	I_C=-2A; I_B=-100mA			-0.40	V
$V_{CEsat-4}$	Collector-emitter saturation voltage	I_C=-3A; I_B=-75mA			-1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-1A; I_B=-50mA			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-30V; I_E=0			-0.1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-0.1	μA
h_{FE-1}	DC current gain	I_C=-0.5A ; V_{CE}=-2V	150		600	
h_{FE-2}	DC current gain	I_C=-3A ; V_{CE}=-2V	70			
f_T	Transition frequency	I_C=-50mA ; V_{CE}=-10V		75		MHz
C_{OB}	Collector output capacitance	I_E=0;f=1MHz ; V_{CB}=-10V		60		pF

PACKAGE OUTLINE

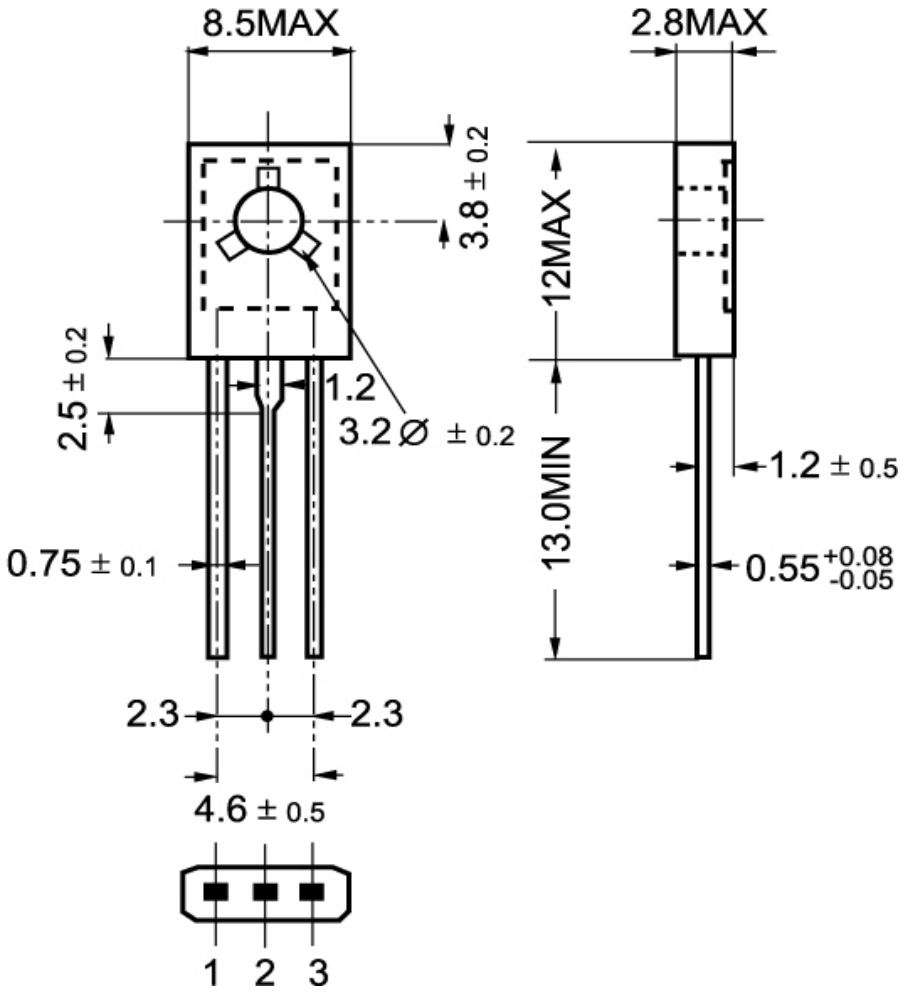

Fig.2 Outline dimensions